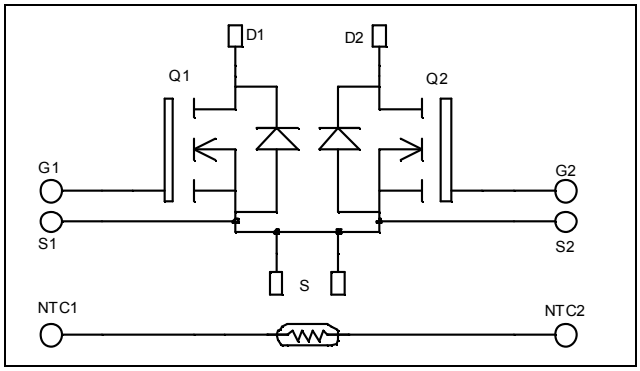
APTM100DU18T

Dual Common Source MOSFET Power Module

V_{DSS} = 1000V
R_{DSon} = 180mΩ max @ Tj = 25°C
I_D = 43A @ Tc = 25°C

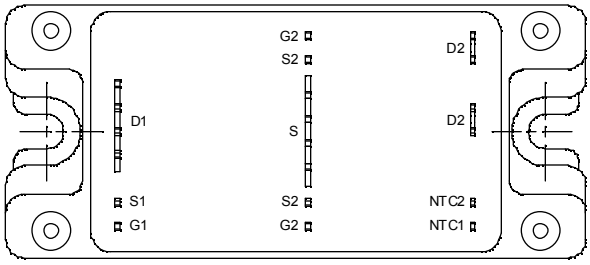


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7® MOSFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		1000	V
I_D	Continuous Drain Current	T_c = 25°C	43	A
		T_c = 80°C	33	
I_{DM}	Pulsed Drain current		172	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		180	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	780	W
I_{AR}	Avalanche current (repetitive and non repetitive)		25	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
BV_{DSS}	Drain - Source Breakdown Voltage	V_{GS} = 0V, I_D = 500µA		1000			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 1000V	T_j = 25°C			500	µA
		V_{GS} = 0V, V_{DS} = 800V	T_j = 125°C			2000	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 21.5A				180	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 5mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±150	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		10.4		nF
C_{oss}	Output Capacitance			1.76		
C_{rss}	Reverse Transfer Capacitance			0.32		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 500V I_D = 43A		372		nC
Q_{gs}	Gate – Source Charge			48		
Q_{gd}	Gate – Drain Charge			244		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 670V I_D = 43A R_G = 2.5Ω		18		ns
T_r	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			155		
T_f	Fall Time			40		
E_{on}	Turn-on Switching Energy ❶	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 670V I_D = 43A, R_G = 2.5Ω		1800		µJ
E_{off}	Turn-off Switching Energy ❷			1246		
E_{on}	Turn-on Switching Energy ❶	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 670V I_D = 43A, R_G = 2.5Ω		2846		µJ
E_{off}	Turn-off Switching Energy ❷			1558		

Source - Drain diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_S	Continuous Source current (Body diode)		Tc = 25°C			43	A
			Tc = 80°C			33	
V_{SD}	Diode Forward Voltage	V_{GS} = 0V, I_S = - 43A				1.3	V
dv/dt	Peak Diode Recovery ❸					10	V/ns
t_{rr}	Reverse Recovery Time	I_S = - 43A, V_R = 500V di_S/dt = 200A/µs			1170		ns
Q_{rr}	Reverse Recovery Charge				32.5		µC

❶ E_{on} includes diode reverse recovery.
❷ In accordance with JEDEC standard JESD24-1.
❸ dv/dt numbers reflect the limitations of the circuit rather than the device itself.
$I_S \le$ - 43A di/dt ≤ 700A/µs $V_R \le V_{DSS}$ $T_j \le$ 150°C

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case					0.16	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5			4.7	N.m
Wt	Package Weight					160	g

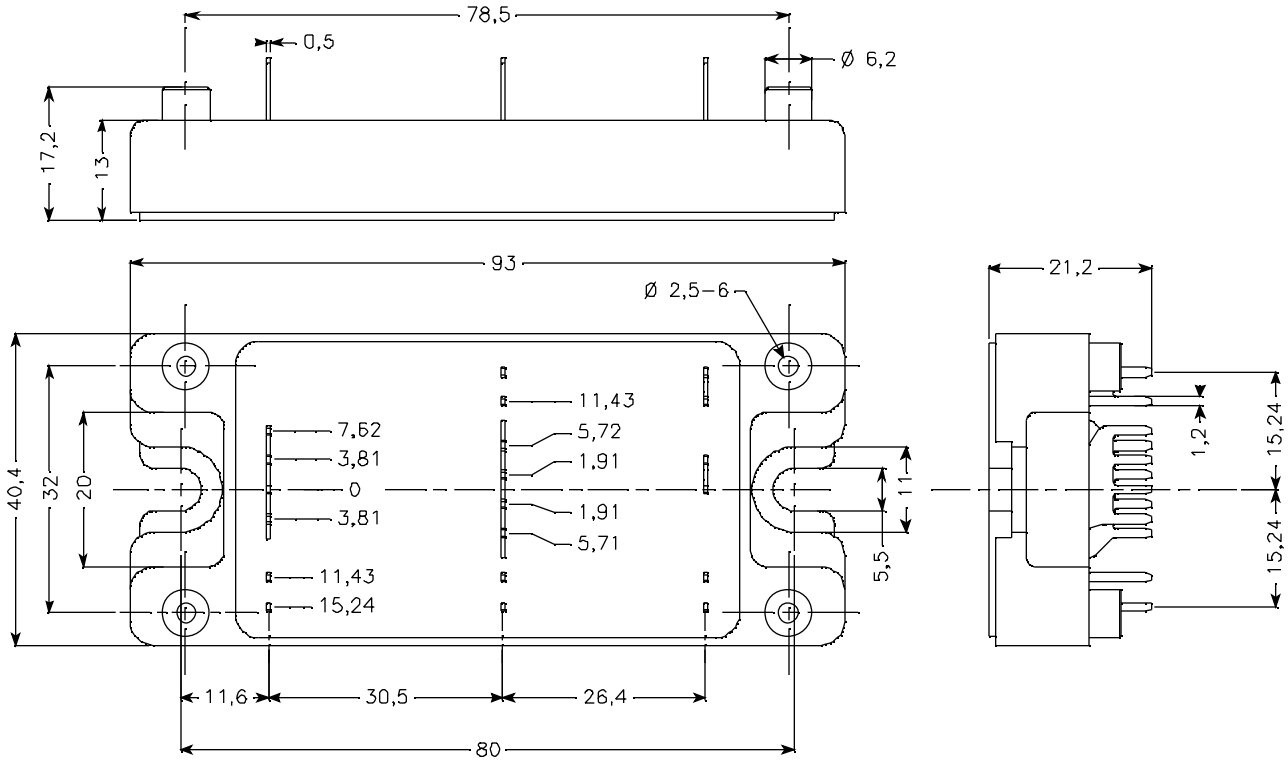
Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		68		kΩ
$B_{25/85}$	T_{25} = 298.16 K		4080		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

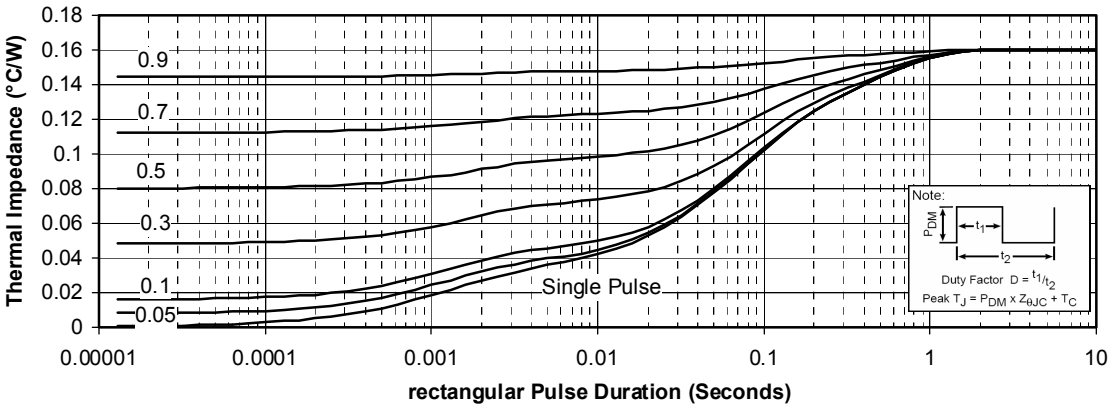
T: Thermistor temperature
R_T: Thermistor value at T

Package outline

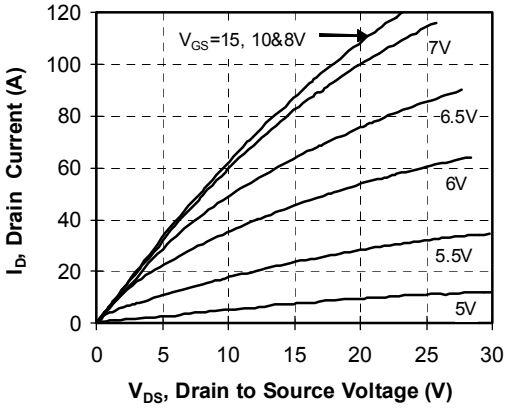


Typical Performance Curve

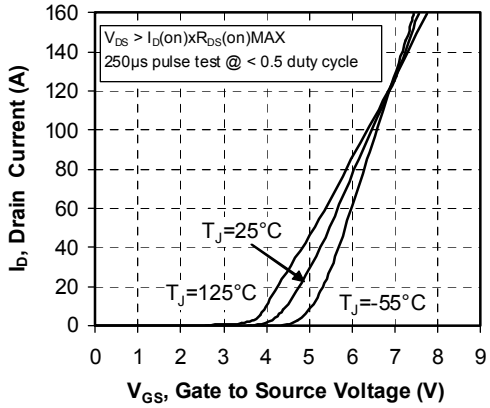
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



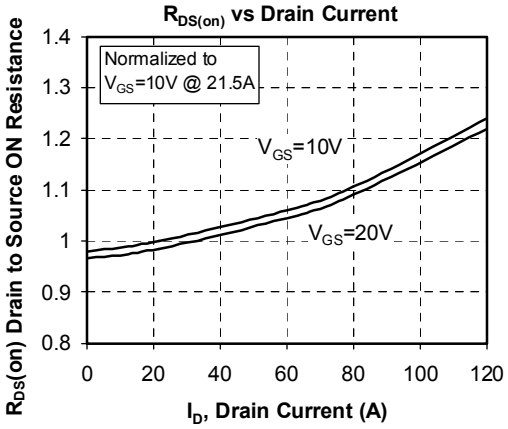
Low Voltage Output Characteristics



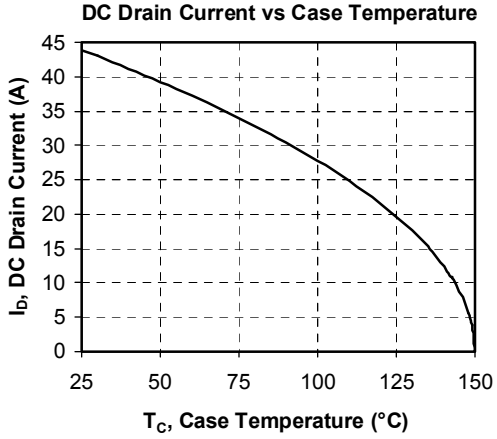
Transfert Characteristics



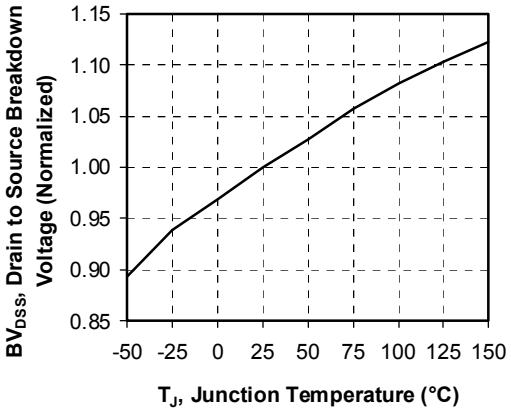
$R_{DS(on)}$ vs Drain Current



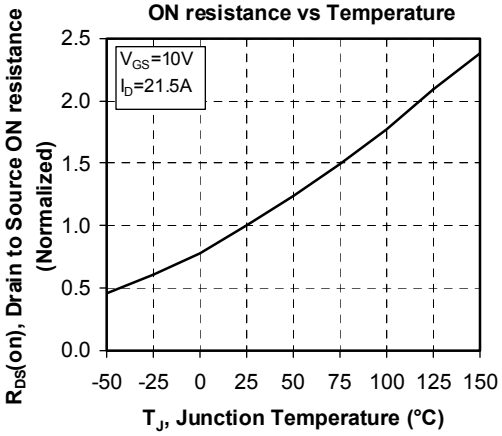
DC Drain Current vs Case Temperature



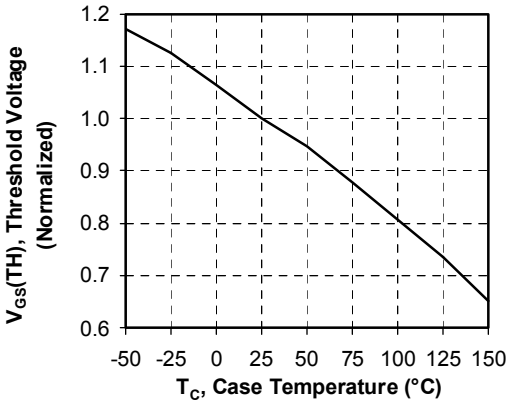
Breakdown Voltage vs Temperature



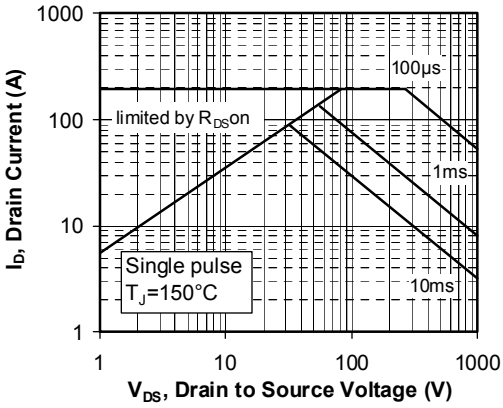
ON resistance vs Temperature



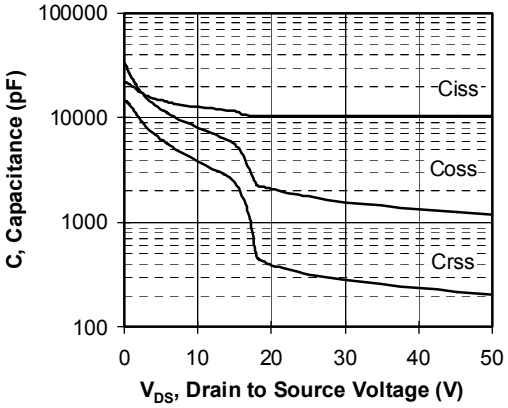
Threshold Voltage vs Temperature



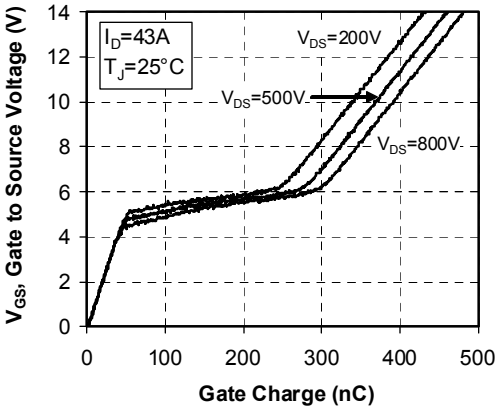
Maximum Safe Operating Area



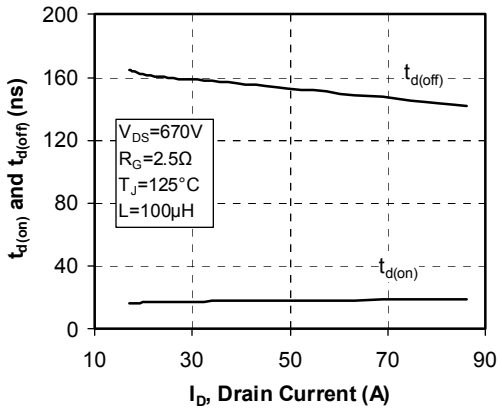
Capacitance vs Drain to Source Voltage



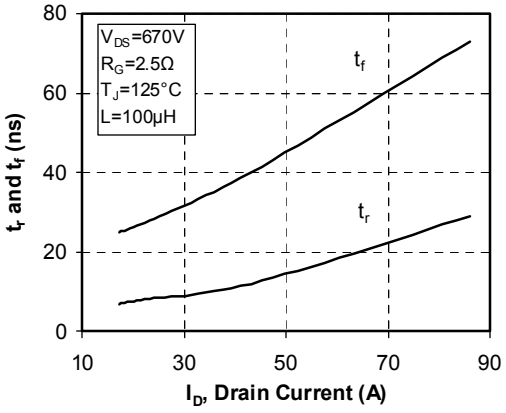
Gate Charge vs Gate to Source Voltage



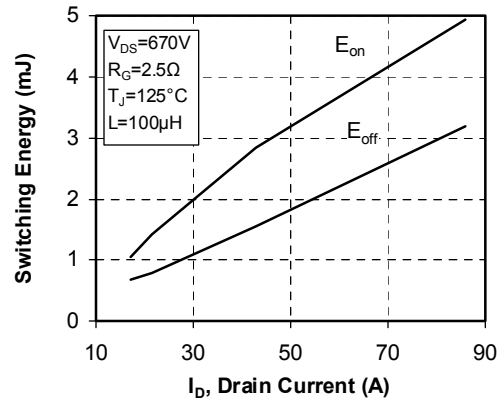
Delay Times vs Current



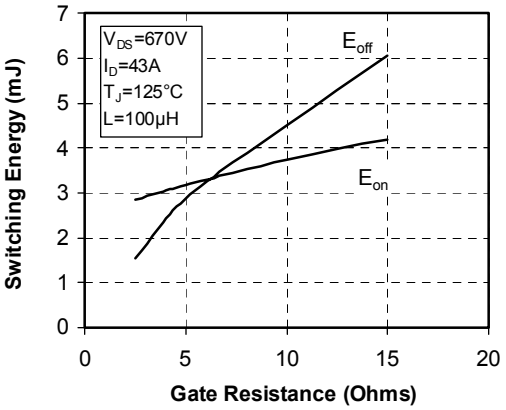
Rise and Fall times vs Current



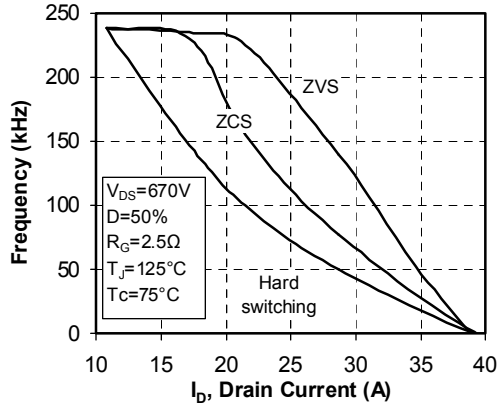
Switching Energy vs Current



Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage